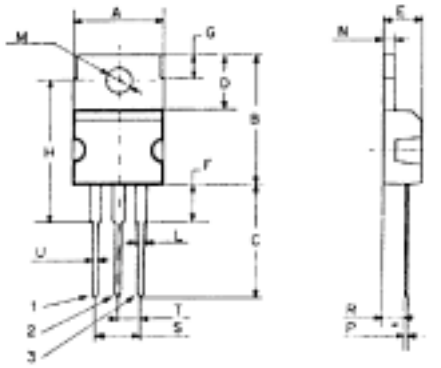
# MRF260

# SILICON NPN RF POWER TRANSISTOR

## DESCRIPTION:

The **ASI MRF260** is Designed for VHF Large Signal Power Amplifier Applications.

## PACKAGE STYLE TO-220



1 = BASE 2 = EMITTER 3 = COLLECTOR MOUNTING TAB = EMITTER

| | DIMENSIONS | | | |
|---|---|---|---|---|
| | mm | | inches | |
| | min | max | min | max |
| A | 10 | 10.4 | 0.393 | 0.409 |
| B | 15.2 | 15.9 | 0.598 | 0.626 |
| C | 12.7 | 13.7 | 0.500 | 0.539 |
| D | 6.2 | 6.6 | 0.244 | 0.260 |
| E | 4.4 | 4.6 | 0.173 | 0.181 |
| F | 3.5 | 5.5 | 0.137 | 0.216 |
| G | 2.65 | 2.95 | 0.104 | 0.116 |
| H | 17.6 typ. | | 0.692 typ. | |
| L | 1.14 | 1.7 | 0.044 | 0.067 |
| M | 3.75 | 3.85 | 0.147 | 0.151 |
| N | 1.23 | 1.32 | 0.048 | 0.051 |
| P | 0.41 | 0.64 | 0.016 | 0.025 |
| R | 2.4 | 2.72 | 0.094 | 0.107 |
| S | 4.95 | 5.15 | 0.194 | 0.203 |
| T | 2.4 | 2.7 | 0.094 | 0.106 |
| U | 0.61 | 0.94 | 0.024 | 0.037 |

## MAXIMUM RATINGS

| | |
|---|---|
| $I_C$ | 1.0 A (CONT) |
| $V_{CE}$ | 18 V |
| $P_{DISS}$ | 12 W @ $T_C$ = 25 $^O$C |
| $T_J$ | -65 $^O$C to +150 $^O$C |
| $T_{STG}$ | -65 $^O$C to +150 $^O$C |
| $\theta_{JC}$ | 14.6 $^O$C/W |

## CHARACTERISTICS $T_C$ = 25 $^O$C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|---|---|---|---|---|---|
| $BV_{CEO}$ | $I_C$ = 10 mA | 18 | | | V |
| $BV_{CES}$ | $I_C$ = 5.0 mA | 36 | | | V |
| $I_{CBO}$ | $V_{CE}$ = 15 V | | | 0.25 | mA |
| $I_{EBO}$ | $V_{EB}$ = 4.0 V | | | 1.0 | mA |
| $h_{FE}$ | $V_{CE}$ = 5.0 V $I_C$ = 250 mA | 5.0 | | | --- |
| $C_{ob}$ | $V_{CB}$ = 15 V f = 1.0 MHz | | | 20 | pF |
| $G_{PE}$ | $V_{CC}$ = 12.5 V $P_{out}$ = 5.0 W f = 175 MHz | 10 | 11 | | dB |
| $\eta$ | | 55 | | | % |

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